

Title (en)
METHOD FOR PRODUCING AN ARTIFICIAL SAPPHIRE SINGLE CRYSTAL

Title (de)
VERFAHREN ZUR HERSTELLUNG EINES KÜNSTLICHEN SAPHIR-EINKRISTALLS

Title (fr)
PROCÉDÉ DE PRODUCTION D'UN MONOCRISTAL DE SAPHIR ARTIFICIEL

Publication
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Application
EP 21840775 A 20211228

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Abstract (en)
[origin: WO2022140808A1] The invention relates to a method for producing an artificial sapphire single crystal. Starting with the step of crystal growth, a temperature difference ΔT , selected from a range of 1 °C to 60 °C, is set between an Al₂O₃ melt surface and a boundary surface of the growing sapphire single crystal to the Al₂O₃ melt, and this temperature difference ΔT is kept constant at least over a greater part of the duration of the crystal growth.

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